

### 50A, 1200V Hyperfast Diode

The RHRU50120 (TA49100) are hyperfast diodes with soft recovery characteristics ( $t_{RR} < 85\text{ns}$ ). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

### Ordering Information

#### PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RHRU50120	TO-218	RHRU50120

NOTE: When ordering, use the entire part number.

### Features

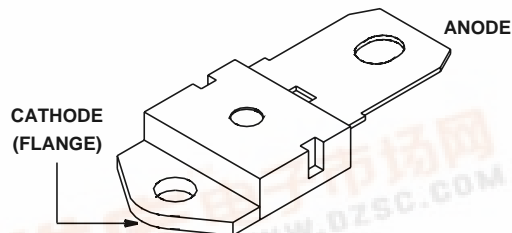
- Hyperfast with Soft Recovery .....<85ns
- Operating Temperature ..... +175°C
- Reverse Voltage .....1200V
- Avalanche Energy Rated
- Planar Construction

### Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

### Package

SINGLE LEAD JEDEC STYLE TO-218



### Symbol



### Absolute Maximum Ratings $T_C = +25^\circ\text{C}$ , Unless Otherwise Specified

	RHRU50120	UNITS
Peak Repetitive Reverse Voltage.....	$V_{RRM}$ 1200	V
Working Peak Reverse Voltage.....	$V_{RWM}$ 1200	V
DC Blocking Voltage.....	$V_R$ 1200	V
Average Rectified Forward Current.....	$I_{F(AV)}$ 50	A
( $T_C = 50^\circ\text{C}$ )		
Repetitive Peak Surge Current.....	$I_{FSM}$ 100	A
(Square Wave, 20kHz)		
Nonrepetitive Peak Surge Current.....	$I_{FSM}$ 500	A
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation.....	$P_D$ 150	W
Avalanche Energy (See Figures 10 and 11).....	$E_{AVL}$ 50	mj
Operating and Storage Temperature.....	$T_{STG}, T_J$ -65 to +175	°C



# RHRU50120

## Electrical Specifications $T_C = +25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRU50120 LIMITS			UNITS
		MIN	TYP	MAX	
$V_F$	$I_F = 50\text{A}$ , $T_C = +25^\circ\text{C}$	-	-	3.2	V
	$I_F = 50\text{A}$ , $T_C = +150^\circ\text{C}$	-	-	2.6	V
$I_R$	$V_R = 1200\text{V}$ , $T_C = +25^\circ\text{C}$	-	-	500	$\mu\text{A}$
	$V_R = 1200\text{V}$ , $T_C = +150^\circ\text{C}$	-	-	1.0	mA
$t_{RR}$	$I_F = 1\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	85	ns
	$I_F = 50\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns
$t_A$	$I_F = 50\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$	-	50	-	ns
$t_B$	$I_F = 50\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$	-	40	-	ns
$Q_{RR}$	$I_F = 50\text{A}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$	-	240	-	nC
$C_J$	$V_R = 10\text{V}$ , $I_F = 0\text{A}$	-	150	-	pF
$R_{\theta JC}$		-	-	1.0	$^\circ\text{C}/\text{W}$

### DEFINITIONS

- $V_F$  = Instantaneous forward voltage ( $p_w = 300\mu\text{s}$ ,  $D = 2\%$ ).
- $I_R$  = Instantaneous reverse current.
- $t_{RR}$  = Reverse recovery time (See Figure 2), summation of  $t_A + t_B$ .
- $t_A$  = Time to reach peak reverse current (See Figure 2).
- $t_B$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 2).
- $Q_{RR}$  = Reverse recovery charge.
- $C_J$  = Junction Capacitance.
- $R_{\theta JC}$  = Thermal resistance junction to case.
- $E_{AVL}$  = Controlled avalanche energy. (See Figures 10 and 11).
- $p_w$  = pulse width.
- $D$  = duty cycle.

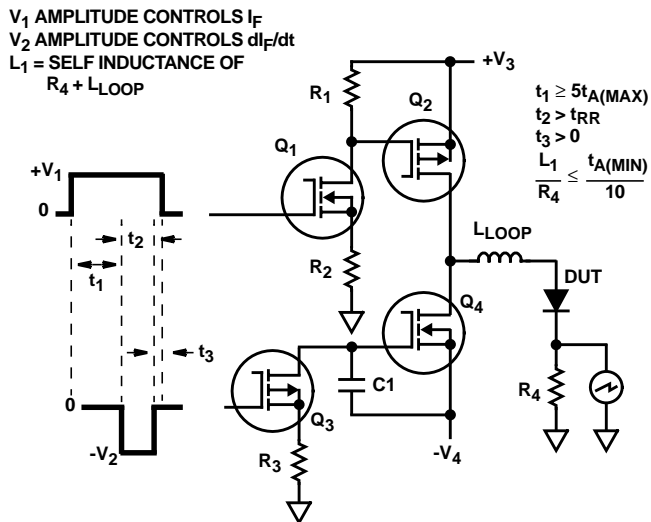


FIGURE 1.  $t_{RR}$  TEST CIRCUIT

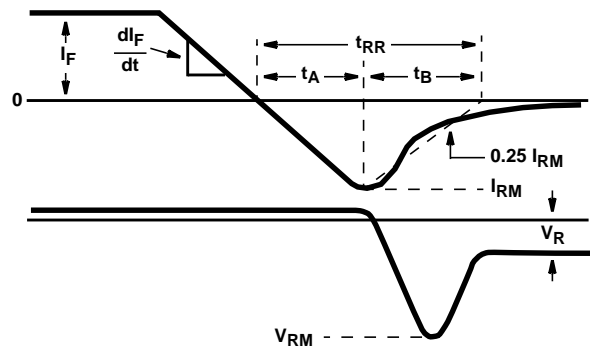


FIGURE 2.  $t_{RR}$  WAVEFORMS AND DEFINITIONS

Typical Performance Curves

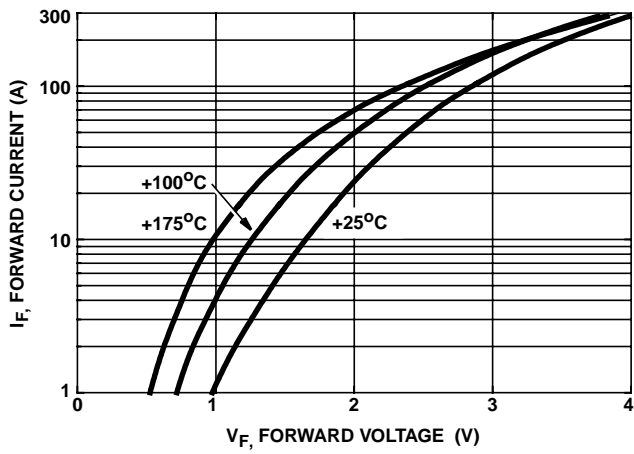


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

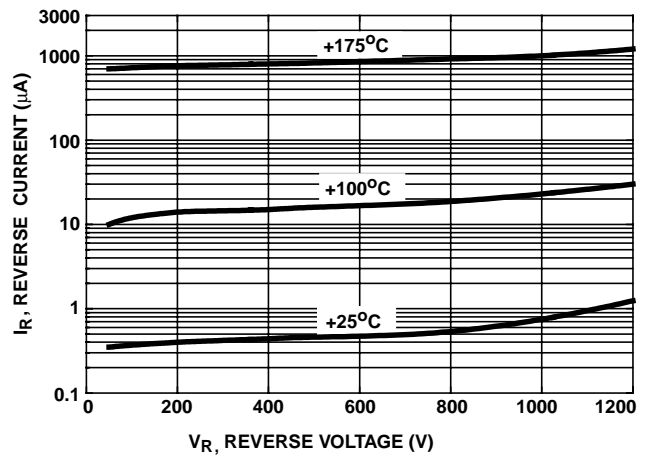


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

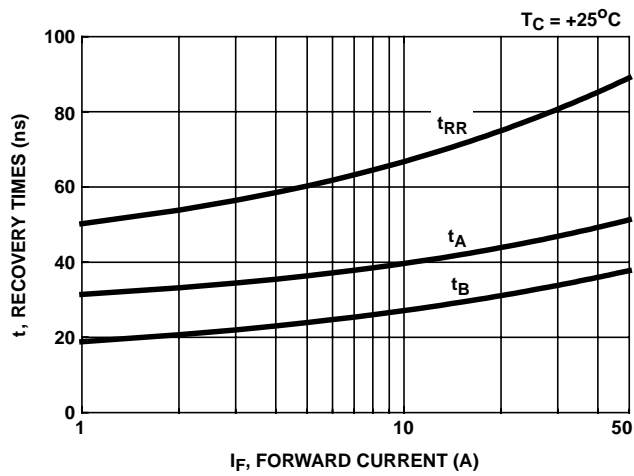


FIGURE 5. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT AT +25°C

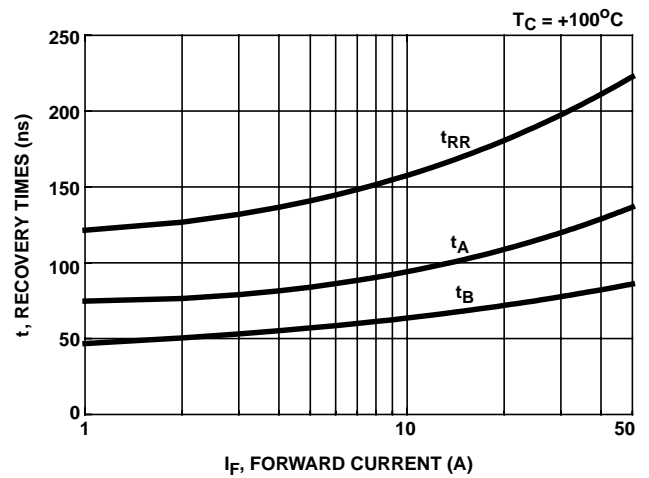


FIGURE 6. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT AT +100°C

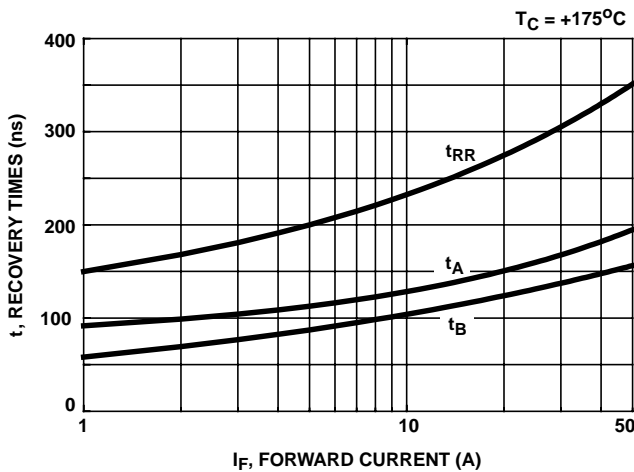


FIGURE 7. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT AT +175°C

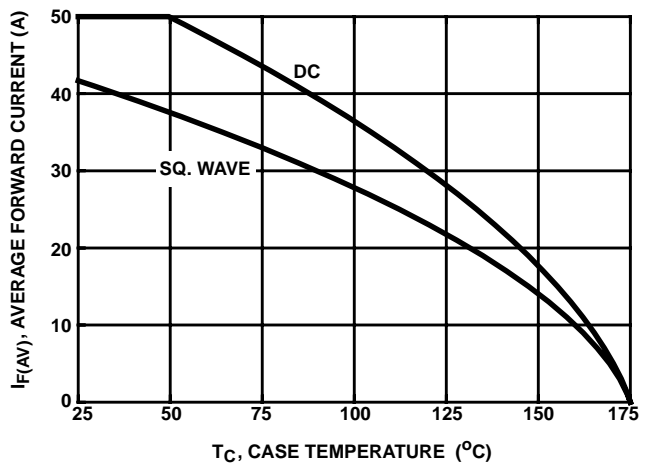


FIGURE 8. CURRENT DERATING CURVE

Typical Performance Curves (Continued)

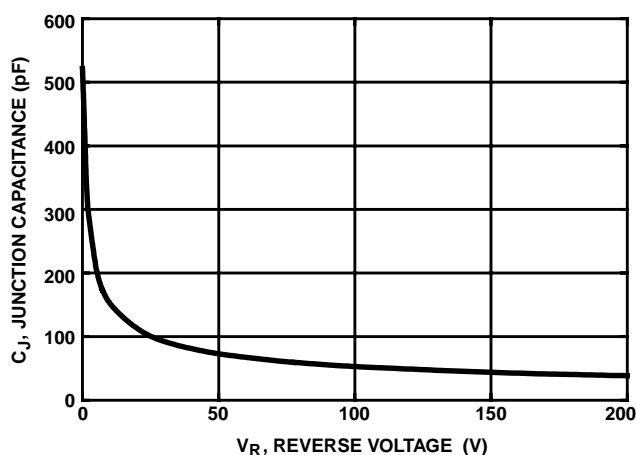


FIGURE 9. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

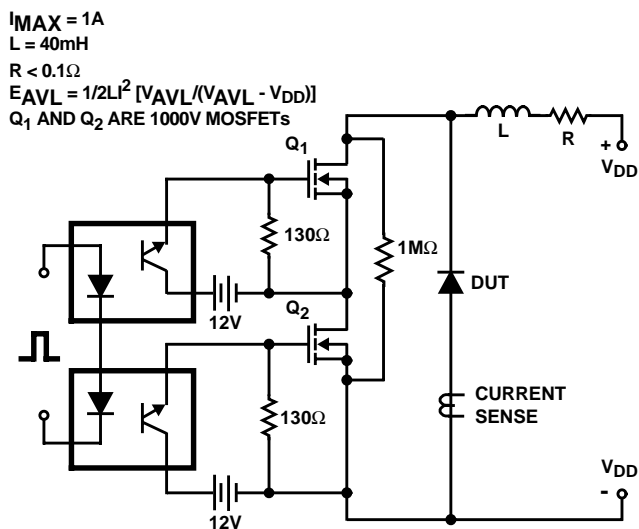


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

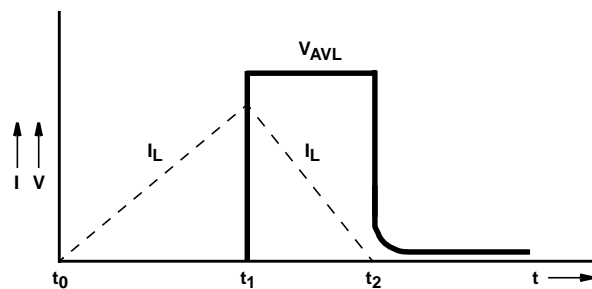


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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